TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON N CHANNEL IGBT

GT30J322

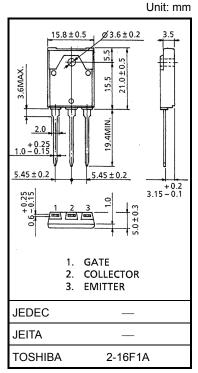
FOURTH-GENERATION IGBT

CURRENT RESONANCE INVERTER SWITCHING APPLICATIONS

- FRD included between emitter and collector
- Enhancement mode type
- High speed : $t_f = 0.25 \mu s$ (Typ.) (IC = 50A)
- Low saturation voltage $: V_{CE} (sat) = 2.1 V (Typ.) (I_C = 50A)$

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT	
Collector-Emitter Voltage		V _{CES}	600	V	
Gate-Emitter Voltage		V _{GES}	±20	V	
Collector Current	DC	IC	30	A	
	1ms	I _{CP}	100		
Emitter-Collector Forward Current	DC	IF	30	A	
	1ms	I _{FP}	60		
Collector Power Dissipation (Tc = 25°C)		P _C	75	W	
Junction Temperature		Tj	150	°C	
Storage Temperature Range		T _{stg}	-55~150	°C	

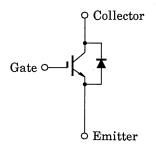


Weight: 5.8 g (typ.)

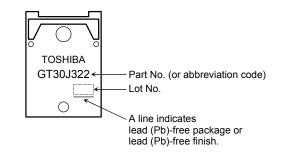
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

EQUIVALENT CIRCUIT



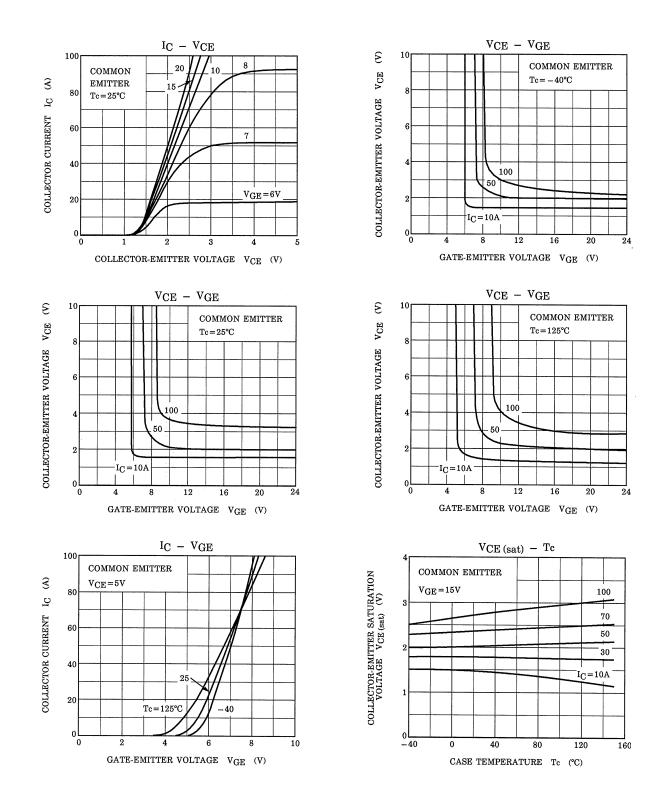
MARKING



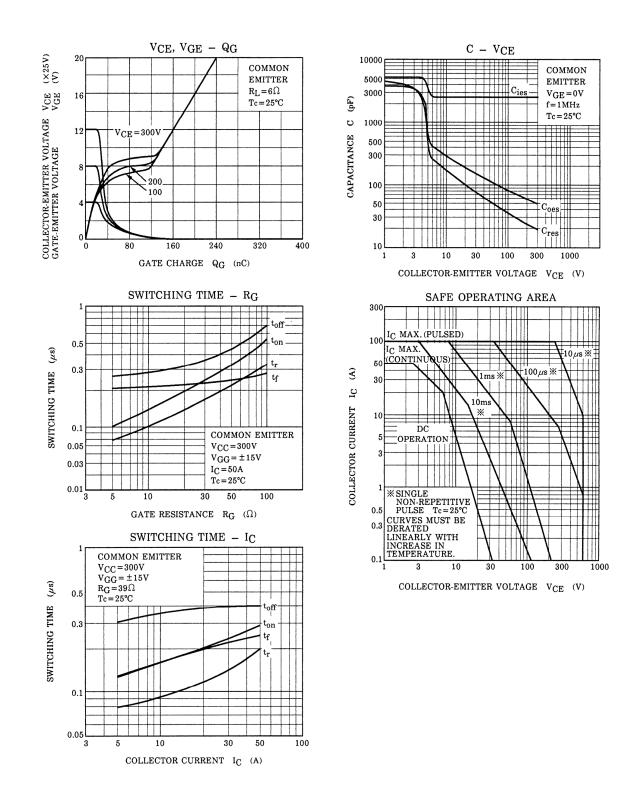
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

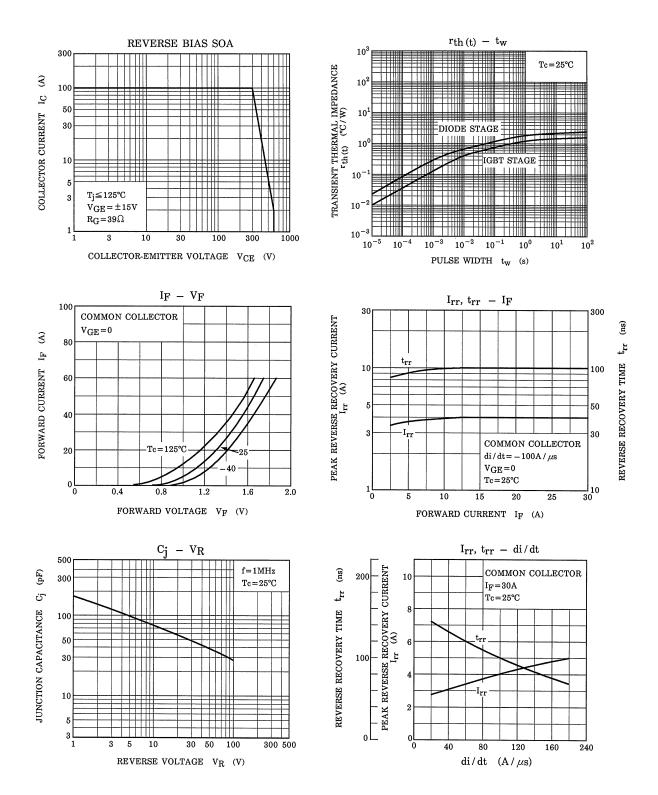
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Gate Leakage Current		I _{GES}	V_{GE} = ±20V, V_{CE} = 0		—	±500	nA
Collector Cut-Off Current		ICES	V _{CE} = 600V, V _{GE} = 0		_	1.0	mA
Gate-Emitter Cut-Off Voltage		V _{GE (OFF)}	I _C = 50mA, V _{CE} = 5V	3.0	_	6.0	V
Collector-Emitter Saturation Voltage		V _{CE (sat)}	I _C = 50A, V _{GE} = 15V	-	2.1	2.8	V
Input Capacitance		Cies	V _{CE} = 10V, V _{GE} = 0, f = 1MHz	-	2500	—	pF
Switching Time	Rise Time	tr		_	0.20	_	μs
	Turn-On Time	t _{on}		_	0.30	—	
	Fall Time	t _f		_	0.25	0.40	
	Turn-Off Time	t _{off}		-	0.40	—	
Peak Forward Voltage		VF	I _F = 30A, V _{GE} = 0	_	_	2.0	V
Reverse Recovery Time		t _{rr}	I _F = 30A, V _{GE} = 0 di / dt = -100A / μs	_	_	0.2	μs
Thermal Resistance (IGBT) Rth (j-c)		R _{th (j−c)}	IGBT	_	_	1.67	°C/W
Thermal Resistance (Diode)		R _{th (j−c)}	Diode	-	_	2.27	°C / W

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